

IN THE CLAIMS

Claim 1-19 (Cancelled).

20 (Currently Amended). An integrated circuit comprising:
a semiconductor structure;
a gate formed on said semiconductor structure; and
a P-type source and a P-type drain region, said source and drain region including both germanium and a P-type source/drain impurity, said source and drain regions ~~region~~ being strained.

21 (Currently Amended). The circuit of claim 20 wherein the ratio of germanium to P-type source/drain impurity ~~impurities~~ is greater than one to one.

22 (Currently Amended). The circuit of claim 20 wherein the ratio of germanium to P-type source/drain impurity ~~impurities~~ is approximately four to one.

23 (Currently Amended). The circuit of claim 20 wherein said source and drain regions are source and drain extensions. ~~P-type impurities are boron impurities.~~

24 (Original). The circuit of claim 20 wherein said source/drain region that includes both boron and germanium is a source/drain extension.